



#### 40V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> T <sub>A</sub> = +25°C
40V	24mΩ @V <sub>GS</sub> = 10V	9.0A
400	$32m\Omega @V_{GS} = 4.5V$	7.8A

## **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

### **Features**

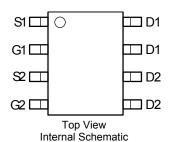
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

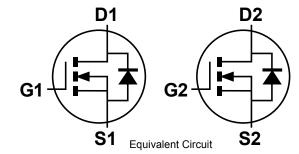
### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (approximate)









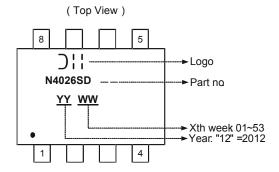
### Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMN4026SSD-13	Standard	SO-8	2,500/Tape & Reel
DMN4026SSDQ-13	Automotive	SO-8	2,500/Tape & Reel

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**





# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	40	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Prain Current (Note 7) V = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	7.0 5.6	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	T<10s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	9.0 7.2	А
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	2.5	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	70	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D	1.3	W	
Total Fower Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	0.8	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	98	°C/W	
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{\theta JA}$	59		
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	D-	1.8	W	
Total Fower Dissipation (Note 1)	T <sub>A</sub> = +70°C	$P_{D}$	1.1		
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	71		
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	11.8		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

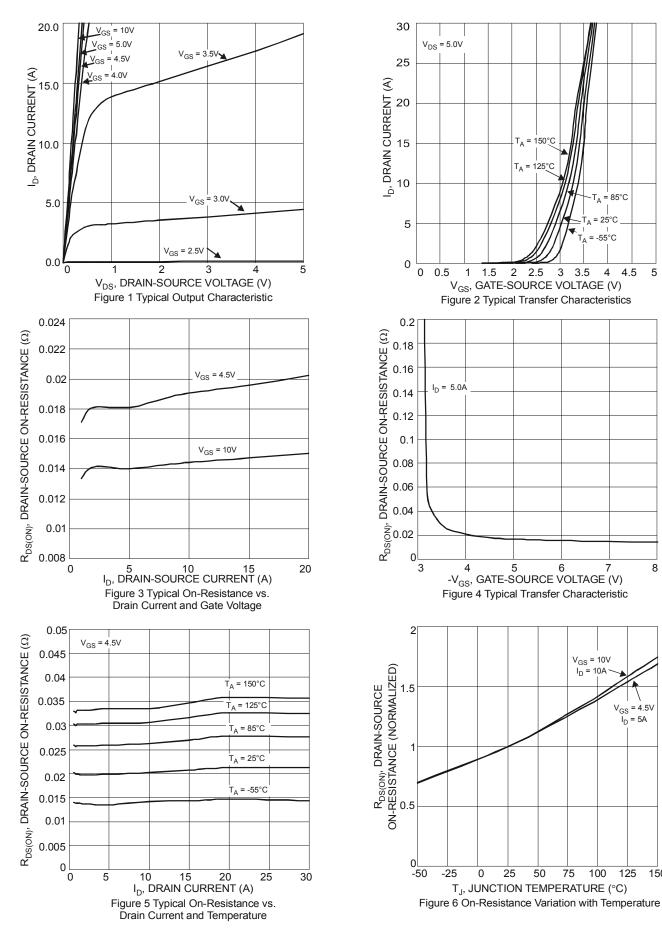
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	15	24	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A	
Static Dialii-Source Oil-Resistance	R <sub>DS(ON)</sub>	_	20	32	11122	$V_{GS} = 4.5V, I_D = 5A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	1060	_		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	84	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	58	_			
Gate Resistance	$R_G$	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	8.8	20		V <sub>DS</sub> = 20V, I <sub>D</sub> = 8A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	19.1	43	nC		
Gate-Source Charge	$Q_{gs}$	_	3.0	7.5	iiC		
Gate-Drain Charge	$Q_{gd}$	_	2.5	6			
Turn-On Delay Time	t <sub>D(on)</sub>		5.3	_		$V_{DD} = 25V, R_L = 2.5\Omega$ $V_{GS} = 10V, R_G = 3\Omega$	
Turn-On Rise Time	t <sub>r</sub>	_	7.1	_	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	15.1	_	113		
Turn-Off Fall Time	t <sub>f</sub>	_	4.8	_			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	10.5	_	nS	I <sub>F</sub> = 8A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Qrr		4.15	_	nC	$I_F = 8A$ , di/dt = 100A/ $\mu$ s	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- ${\bf 8.\ Short\ duration\ pulse\ test\ used\ to\ minimize\ self-heating\ effect.}$
- 9. Guaranteed by design. Not subject to product testing.

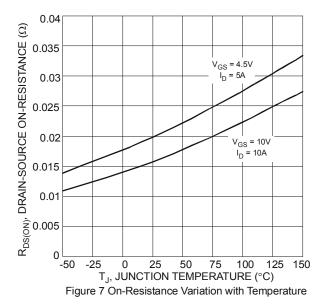


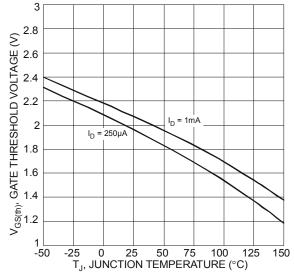


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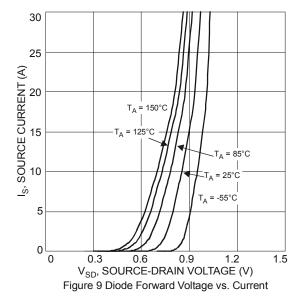
V<sub>GS</sub> = 4.5V I<sub>D</sub> = 5A

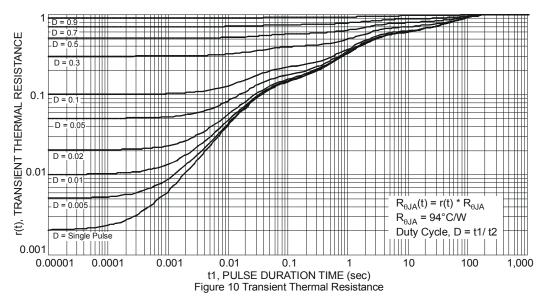








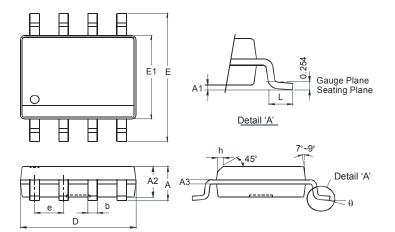






# **Package Outline Dimensions**

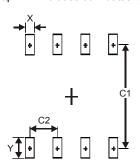
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	1	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Χ	0.60
Υ	1.55
C1	5.4
C2	1 27



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